SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND PROCESS FOR MANUFACTURING THE SAME

ABSTRACT OF THE DISCLOSURE

Over a well region formed over a semiconductor substrate body, there is formed of an epitaxial layer which has a lower impurity concentration than that of an impurity contained in the well region. MOS·FETs are mounted on the epitaxial layer.

A field insulating film is extended in a depth-wise direction to contact with the well region. The MOS·FET have their source/drain regions formed in the epitaxial layer to form a punch-through stopper layer between the sources and drains.

Figures 1 and 42

This Sheet Has Been Replaced

